



Technical Data Data Sheet N1651, Rev. - **Green Products**

RMB2S-RMB6S Miniature Glass Passivated Fast Recovery Surface Mount Bridge Rectifiers

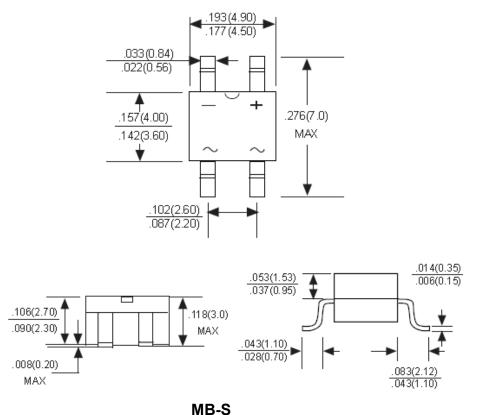
Features:

- Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique
- High temperature soldering guaranteed:260°C/10 seconds at 5 lbs., (2.3kg) tension
- Small size, simple installation
- High surge current capability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Data:

- Case: Molded plastic body
- Terminals: Plated leads solderable per MIL-STD-750, Method 2026
- Polarity: Polarity symbols marked on case
- Mounting Position: Any
- Weight: 0.0044 ounce, 0.126 grams

Mechanical Dimensions: In Inches/mm





China - Germany - Korea - Singapore - United States http://www.smc-diodes.com - sales@ smc-diodes.com -

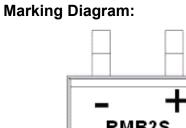


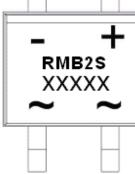
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Where XXXXX is YYWWL

RMB2S	= Part Name
ΥY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
RMB2S-RMB6S	MB-S (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.



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Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified

Single Phase half wave 60Hz, resistive or inductive load. For capacitive load current derate by 20%.

Characteristic	Symbol	RMB2S	RMB4S	RMB6S	Units
Maximum repetitive peak reverse voltage	V _{RRM}	200	400	600	
RMS Reverse Voltage	V _{R(RMS)}	140	280	420	V
Maximum DC blocking voltage	V _{DC}	200	400	600	
Maximum average forward current 60Hz sine save resistance load On glass-epoxy P.C.B. On aluminum substrate	I _{F(AV)}	0.5 0.8		A	
Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	30		A	
Maximum instantaneous forward voltage drop (Note 1)@ $I_F = 0.4A$	V _F	1.0		V	
Maximum DC reverse current $T_A = 25^{\circ}C$ at rated DC blocking voltage $T_A = 125^{\circ}C$	I _R	5 100		μA	
Maximum reverse recovery time(Note 2)	trr 150		nS		
Typical junction capacitance (per leg) Cj			13		pF
Typical thermal resistance	R _{θJA}	85			°C/W
Operating junction and storage temperature range	nd storage temperature range T _J ,T _{STG} -55 to +150		°C		

Note: 1. Pulse Test with PW=300us, 1% Duty Cycle

2. Reverse Recovery Test Condition: I_F =0.5A, I_R =1.0A, I_{RR} =0.25A

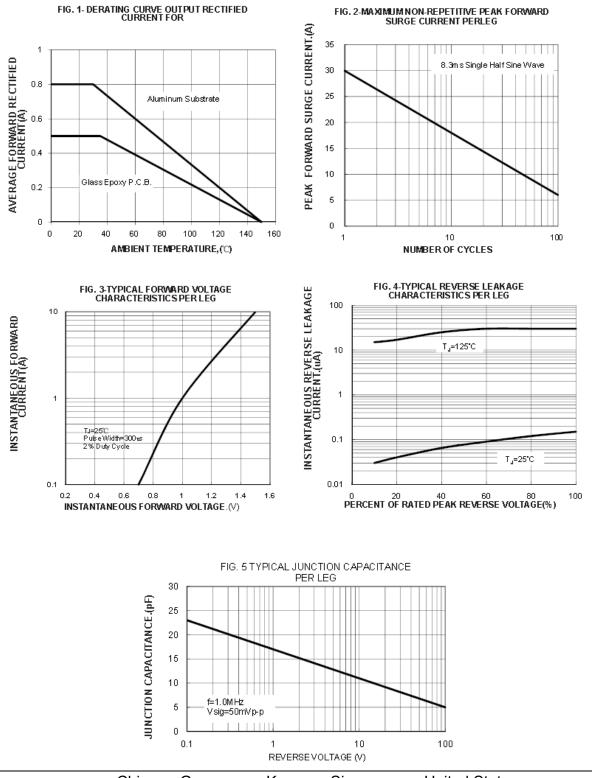


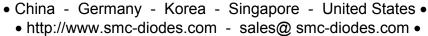
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